

EVVOSEMI[®]

THINK CHANGE DO



ESD



TVS



MOS



LDO



Diode



Sensor



DC-DC

Product Specification

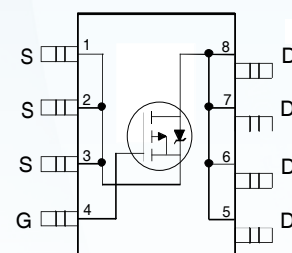
▶ Domestic	Part Number	IRF7406
▶ Overseas	Part Number	IRF7406
▶ Equivalent	Part Number	IRF7406

EV is the abbreviation of name EVVO

P-Channel 30 V (D-S) MOSFET

Description

The SOP-8 has been modified through a customized leadframe for enhanced thermal characteristics and multiple-die capability making it ideal in a variety of power applications. With these improvements multiple devices can be used in an application with dramatically reduced board space. The package is designed for vapor phase, infra red or wave soldering techniques. Power dissipation of greater than 0.8W is possible in a typical PCB mount application.



Top View

Features

- Generation V Technology
- Ultra Low On-Resistance
- P-Channel Mosfet
- Surface Mount
- Available in Tape & Reel
- Dynamic dv/dt Rating
- Fast Switching
- Lead-Free

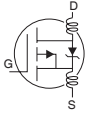
Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_A = 25^\circ\text{C}$	10 Sec. Pulsed Drain Current, $V_{GS} @ -10\text{V}$	-6.7	A
$I_D @ T_A = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -10\text{V}$	-5.8	
$I_D @ T_A = 70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -10\text{V}$	-3.7	
I_{DM}	Pulsed Drain Current ①	-23	
$P_D @ T_A = 25^\circ\text{C}$	Power Dissipation	2.5	W
	Linear Derating Factor	0.02	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
dv/dt	Peak Diode Recovery dv/dt ②	-5.0	V/ns
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	°C

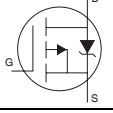
Thermal Resistance Ratings

	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient ④	---	50	°C/W

P-Channel 30 V (D-S) MOSFET
Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-30	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	-0.020	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = -1\text{mA}$
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	—	—	45	Ω	$V_{GS} = -10V, I_D = -2.8A$ ③
		—	—	70		$V_{GS} = -4.5V, I_D = -2.4A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	-1.0	—	—	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
g_{fs}	Forward Transconductance	3.1	—	—	S	$V_{DS} = -15V, I_D = -2.8A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	-1.0	μA	$V_{DS} = -24V, V_{GS} = 0V$
		—	—	-25		$V_{DS} = -24V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	$V_{GS} = -20V$
	Gate-to-Source Reverse Leakage	—	—	100		$V_{GS} = 20V$
Q_g	Total Gate Charge	—	—	59	nC	$I_D = -2.8A$
Q_{gs}	Gate-to-Source Charge	—	—	5.7		$V_{DS} = -2.4V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	21		$V_{GS} = -10V$, See Fig. 6 and 12 ③
$t_{d(on)}$	Turn-On Delay Time	—	16	—	ns	$V_{DD} = -15V$
t_r	Rise Time	—	33	—		$I_D = -2.8A$
$t_{d(off)}$	Turn-Off Delay Time	—	45	—		$R_G = 6.0\Omega$
t_f	Fall Time	—	47	—		$R_D = 5.3\Omega$, See Fig. 10 ③
L_D	Internal Drain Inductance	—	2.5	—	nH	Between lead tip and center of die contact 
L_S	Internal Source Inductance	—	4.0	—		
C_{iss}	Input Capacitance	—	1100	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	490	—		$V_{DS} = -25V$
C_{rss}	Reverse Transfer Capacitance	—	220	—		$f = 1.0\text{MHz}$, See Fig. 5

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-3.1	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	-23		
V_{SD}	Diode Forward Voltage	—	—	-1.0	V	$T_J = 25^\circ\text{C}$, $I_S = -2.0A$, $V_{GS} = 0V$ ②
t_{rr}	Reverse Recovery Time	—	42	63	ns	$T_J = 25^\circ\text{C}$, $I_F = -2.8A$
Q_{rr}	Reverse Recovery Charge	—	64	96	nC	$di/dt = 100A/\mu s$ ③
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② $I_{SD} \leq -2.8A$, $di/dt \leq 90A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 150^\circ\text{C}$
- ③ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.
- ④ Surface mounted on FR-4 board, $t \leq 10\text{sec}$.

P-Channel 30 V (D-S) MOSFET

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

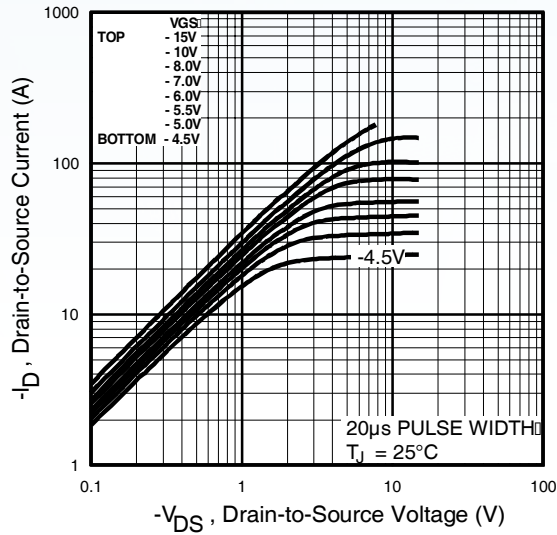


Fig 1. Typical Output Characteristics

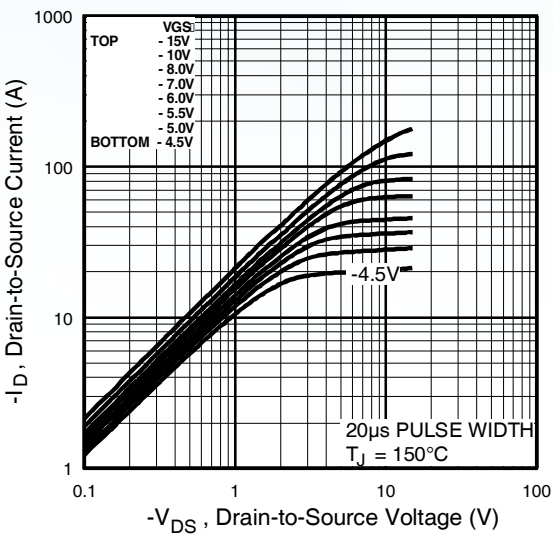


Fig 2. Typical Output Characteristics

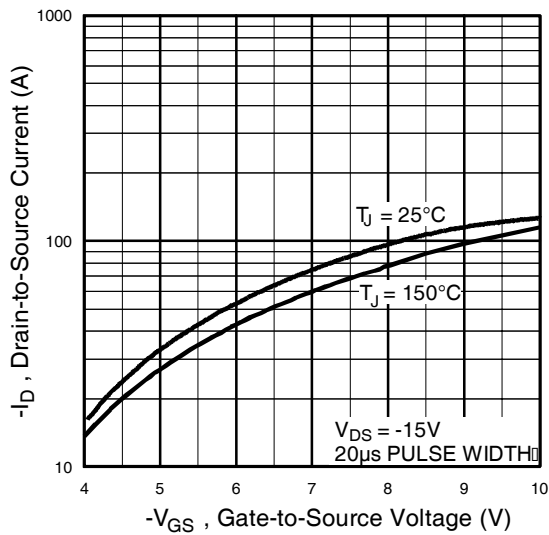


Fig 3. Typical Transfer Characteristics

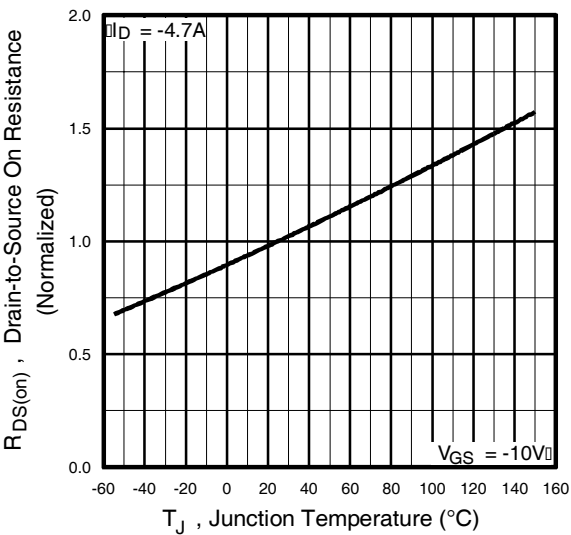


Fig 4. Normalized On-Resistance Vs. Temperature

P-Channel 30 V (D-S) MOSFET

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

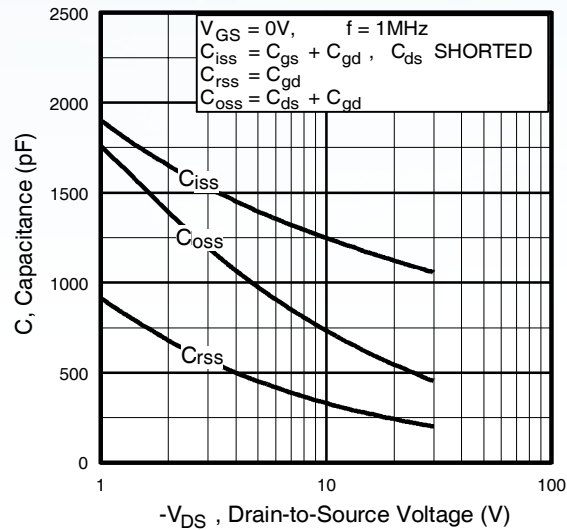


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

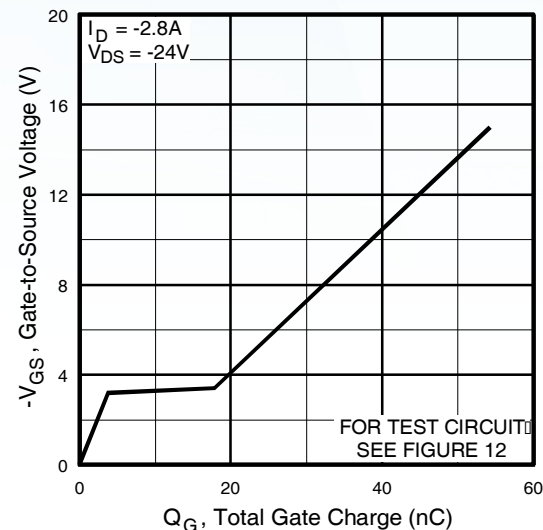


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

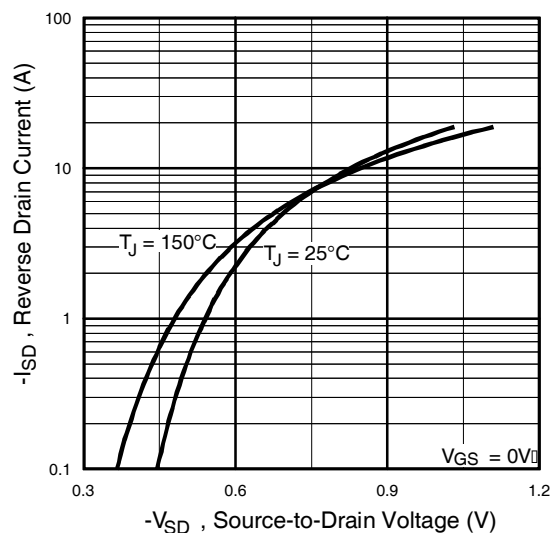


Fig 7. Typical Source-Drain Diode Forward Voltage

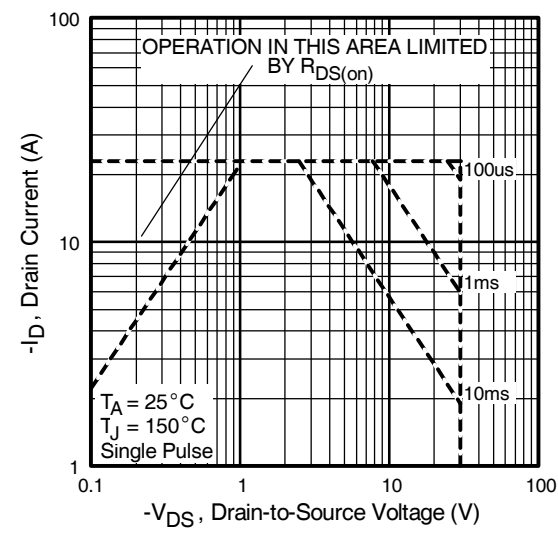


Fig 8. Maximum Safe Operating Area

P-Channel 30 V (D-S) MOSFET

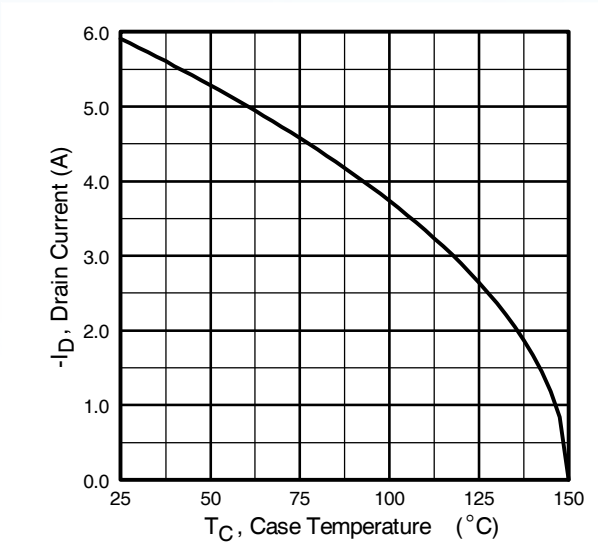


Fig 9. Maximum Drain Current Vs. Ambient Temperature

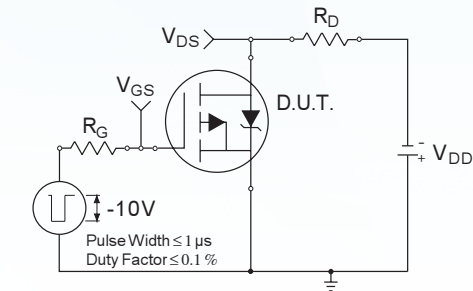


Fig 10a. Switching Time Test Circuit

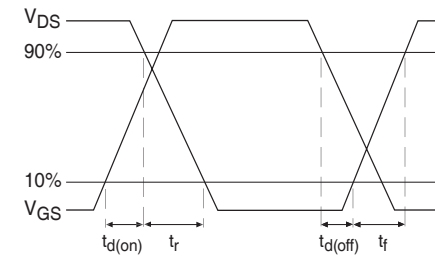
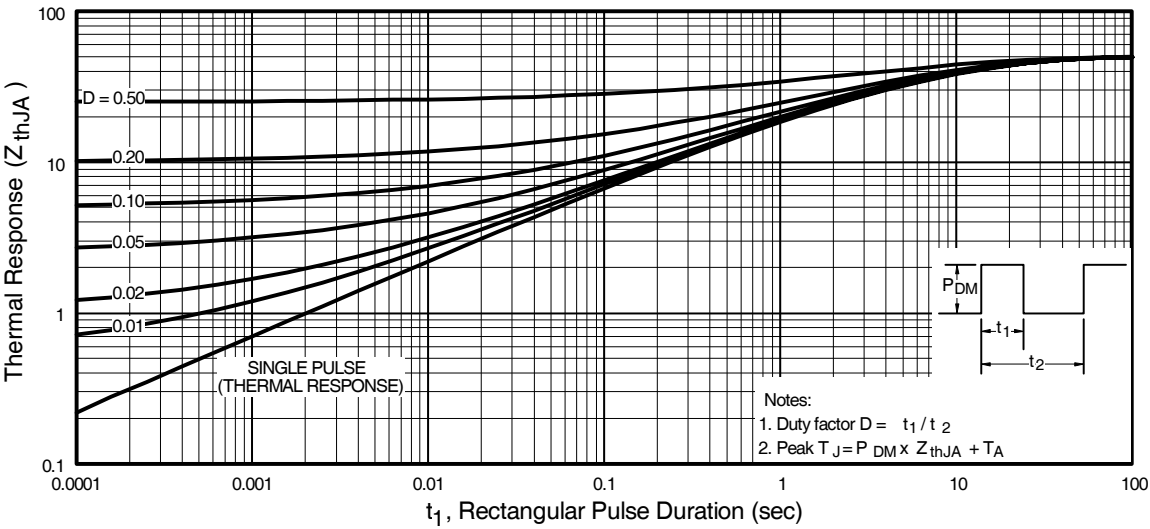


Fig 10b. Switching Time Waveforms



P-Channel 30 V (D-S) MOSFET

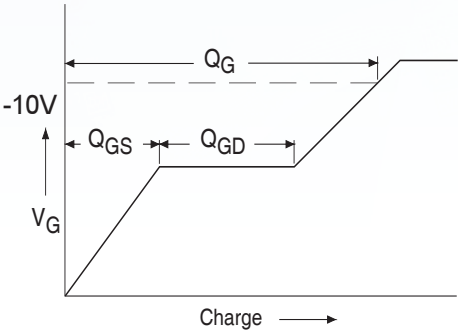


Fig 12a. Basic Gate Charge Waveform

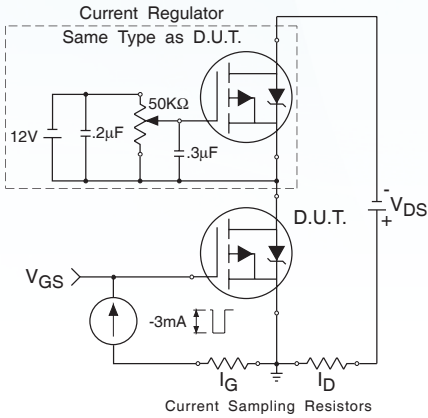
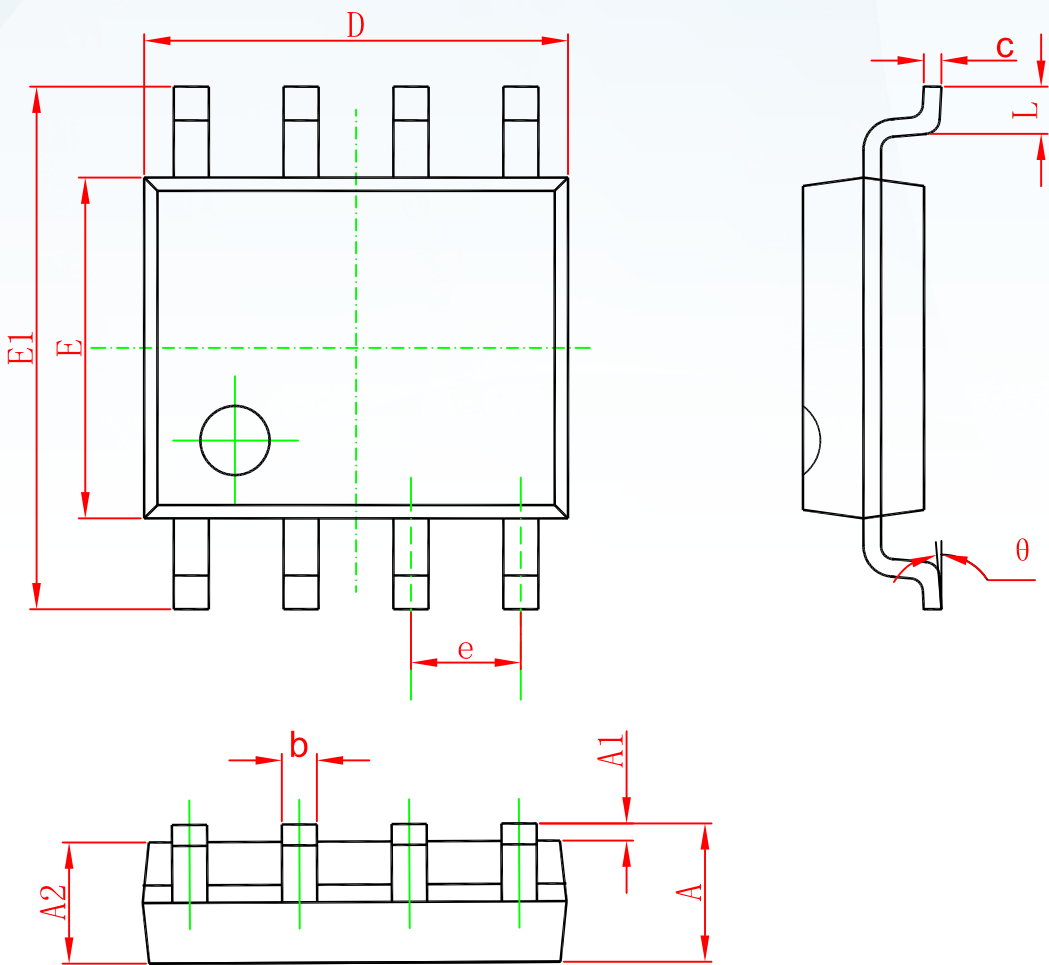


Fig 12b. Gate Charge Test Circuit

P-Channel 30 V (D-S) MOSFET

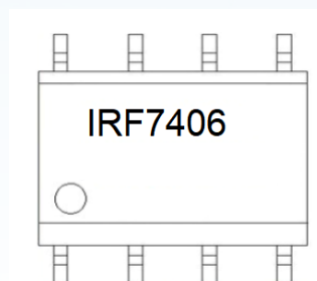
SOP-8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

P-Channel 30 V (D-S) MOSFET

Marking



Ordering information

Order code	Package	Baseqty	Deliverymode
IRF7406	SOP-8	3000	Tape and reel

Disclaimer

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